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inverse t gate

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Wen, D.S.; Hsu, C.C.-H.; Taur, Y.; Zicherman, D.S.; Wordeman, M.R.; Ning, T.
Electron Devices Meeting, 1989. Technical Digest., International , 3-6 Dec. 198
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[Abstract] **[PDF Full-Text (216 KB)] IEEE CNF****2 Self-aligned silicided inverse-T gate LDD devices for sub-half micron technology**

Chen, M.-L.; Hillenius, S.J.; Juengling, W.; Yang, T.S.; Kornblit, A.; Lindenberge W.S.; Swiderski, J.A.; Favreau, D.P.,
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[Abstract] **[PDF Full-Text (352 KB)] IEEE CNF****3 A self-aligned LDD/channel implanted ITLDD process with selectively deposited poly gates for CMOS VLSI**

Pfiester, J.R.; Baker, F.K.; Sivan, R.D.; Crain, N.; Lin, H.-H.; Liaw, M.; Seelbach Gunderson, C.; Denning, D.,
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